

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none/semi standard	
	5.0	Secondary Flat Length	none / 18.5 +/- 2.5mm	Wafer Vendor
	6.0	Overall Thickness	516.50 +/- 6.00 $\mu$ m	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00 $\mu$ m	Guaranteed by Process
	8.0	Bow	<60.00 $\mu$ m	ADE to ASTM F534, 20%
	9.0	Warp	<60.00 $\mu$ m	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
	12.0	Backside Laser Marking Type	On wafer BACKSIDE. Scribe format: [PANORAMA.XXXX] (unique scribe)	Guaranteed by process
HandleSilicon	13.0	Handle Growth Method	CZ	Wafer Vendor
	14.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	15.0	Handle Thickness	500.00 +/- 5.00 $\mu$ m	ADE, 100%
	16.0	Handle Doping Type	N	Wafer Vendor
	17.0	Handle Dopant	Antimony	Wafer Vendor
	18.0	Handle Resistivity	0.01 - 0.02 Ohmcm	Wafer Vendor
	19.0	Backside Finish	Polished with lasermarking and oxide.	Wafer Vendor
	BuriedOxide	20.0	Oxide Type	Thermal
21.0		Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
22.0		Oxide formed on	Handle Wafer	
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	25.0	Nominal Thickness	14.50 +/- 0.50 $\mu$ m	FTIR, 100% 9-Pt (note3)
	26.0	Distance to device silicon edge from wafer edge	<= 2.0 mm	Typical by process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Antimony	Wafer Vendor
	29.0	Device Resistivity	0.01 - 0.02 Ohmcm	Wafer Vendor
	30.0	Voids	0	Bright Light, 100% (note 2)
	31.0	Scratches	0	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information